

BD912

Rev. H Oct.-2018

TO-220

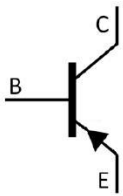
PNP

Silicon PNP transistor in a TO-220 Plastic Package.

, BD911

High V_{CEO} , high I_C , complement to BD911.

Use in power linear and switching applications.



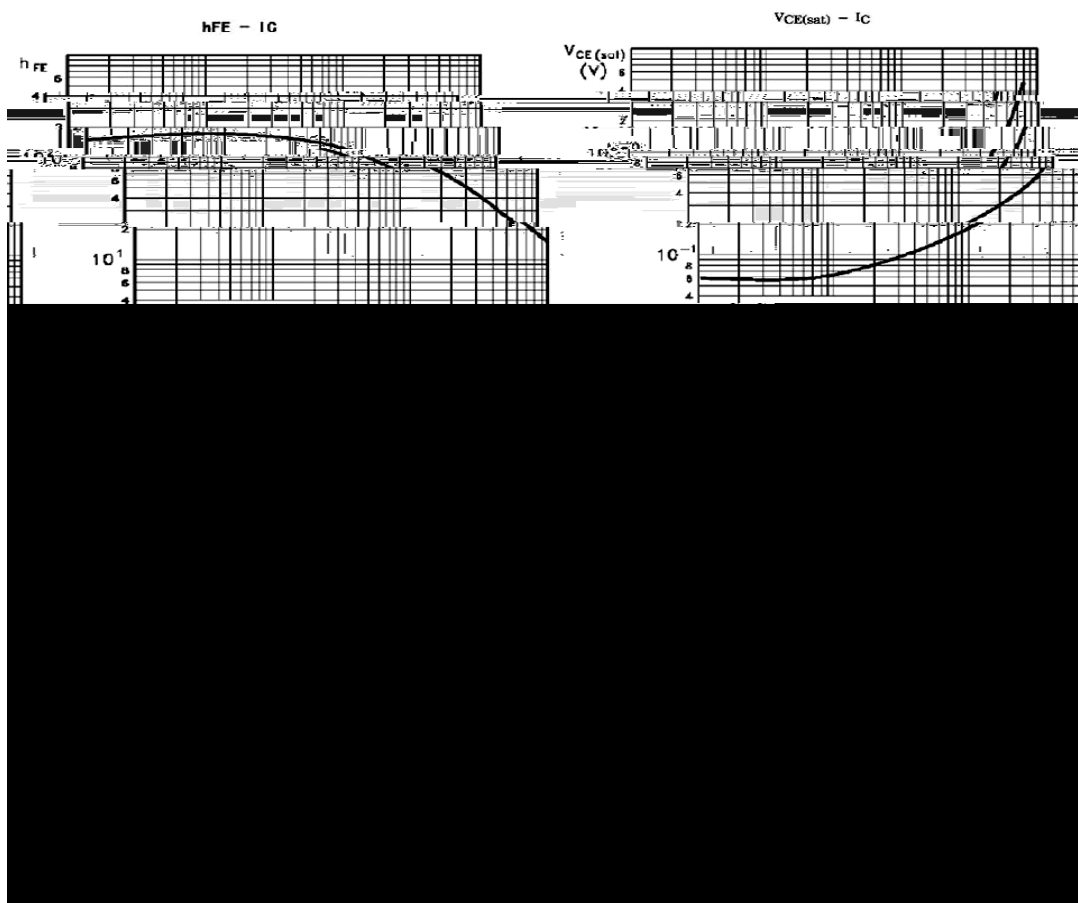
PIN 1 Base PIN 2 Collector PIN 3 Emitter

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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-15	A
Base Current – Continuous	I_B	-5.0	A
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	90	W
Junction Temperature	T_j	150 T	

/ Electrical Characteristic Curve

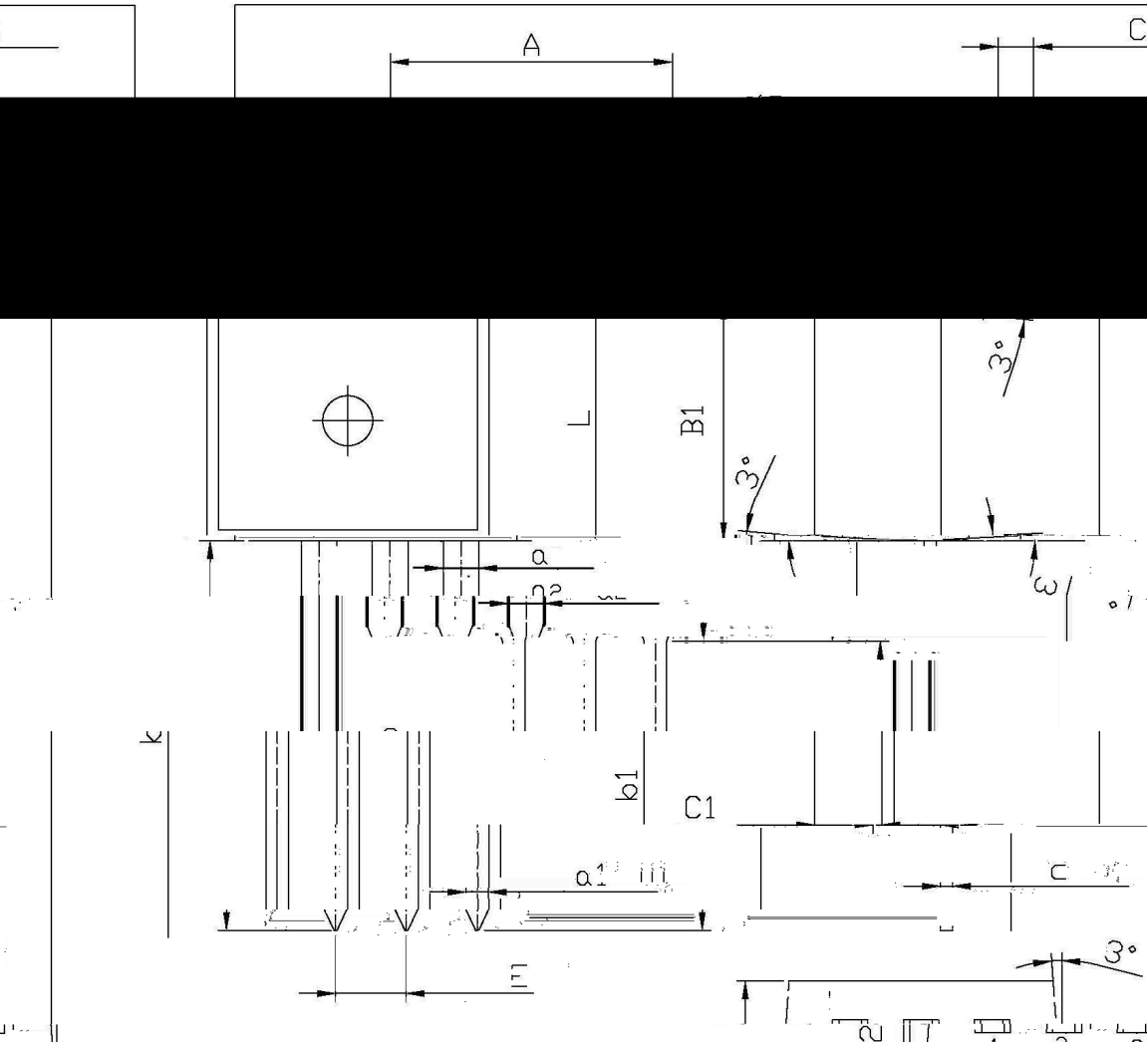


/ Package Dimensions

mm

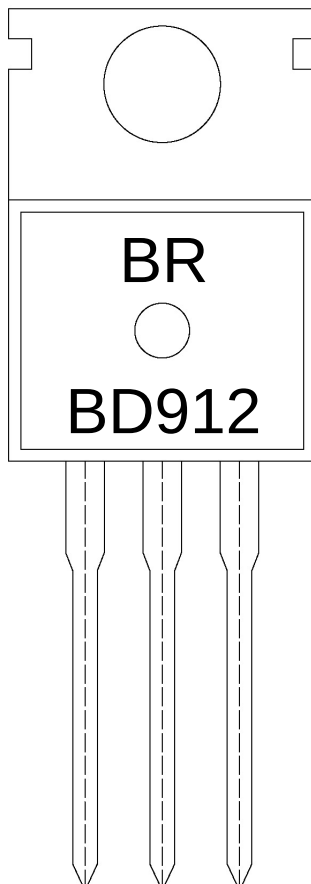
TO-220

单位:



Dimensions in Millimeters			Dimensions in Millimeters		
Symbol	Min	Max	Symbol	Min	Max
A	9.8	10.2	C	1.2	1.4
B	3.56	3.64	B1	6.3	6.7
a	9.0	9.4	F	15.7	16.1
b1	1.22	1.32	h1	1.25	1.45
C1	0.4	0.6	a1	1.25	1.45

/ Marking Instructions



BR

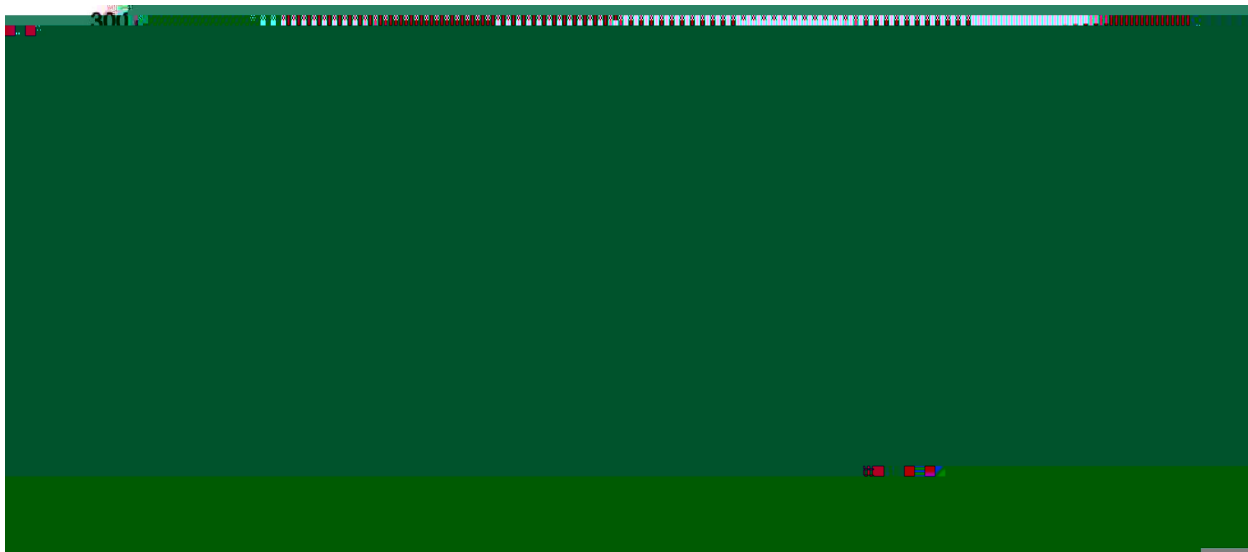
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Note:

BR: Company Code

BD912: Product Type.

****: Lot No. Code, code change with Lot No.


() / Temperature Profile for Dip Soldering(Pb-Free)


Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec
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/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱